

DESCRIPTION

The SS6200 is a single Phase MOSFET gate driver optimized to drive the gates of both high-side and low-side power MOSFETs.

The integrated bootstrap diode reduces external component count. With a wide operating voltage range, high or low side MOSFET gate drive voltage can be optimized for the best efficiency. Internal adaptive non-overlap circuit further reduces switching losses by preventing simultaneous conduction of both MOSFETs.

The UVLO circuits prevent malfunction when VCC is lower than the specified threshold voltage.

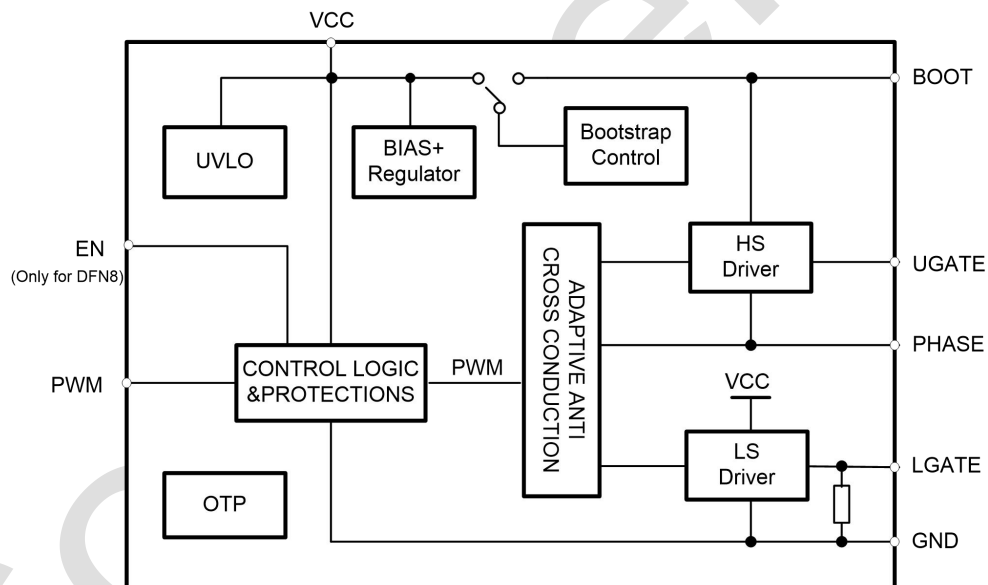
FEATURES

- Drive two N-MOSFETs
- High-Frequency operation (Up to 1MHz)
- PWM input capable of 3.3V and 5V
- Fast output rise time
- Internal bootstrap diode
- Adaptive shoot through protection
- Under-voltage lockout
- Internal thermal shutdown
- Small size package: SOP8, DFN2x2-8L
- These are Pb-Free Devices

APPLICATIONS

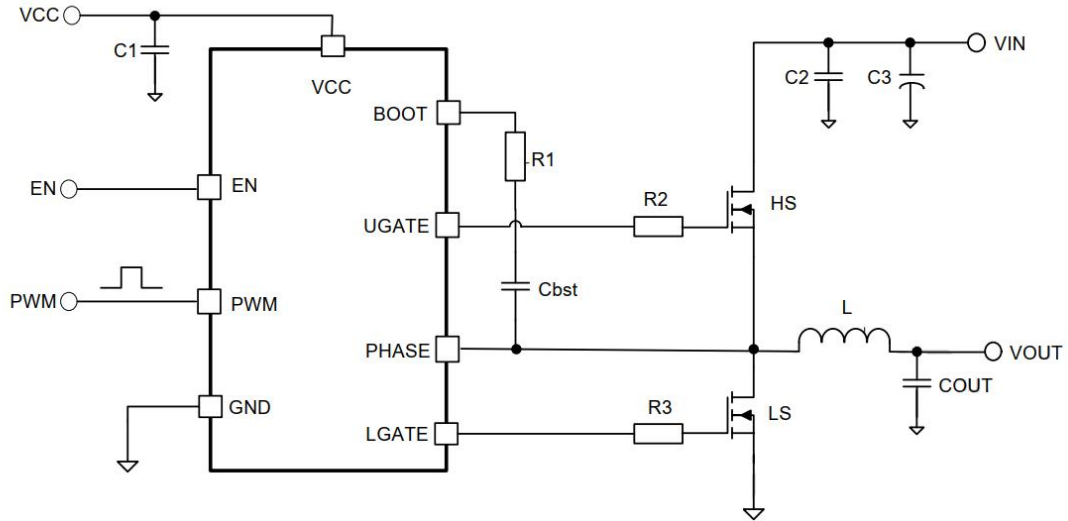
- Wireless Charger for 5W to 20W Systems
- Half or full bridge driver for N+N MOSFET

BLOCK DIAGRAM



APPLICATION CIRCUIT

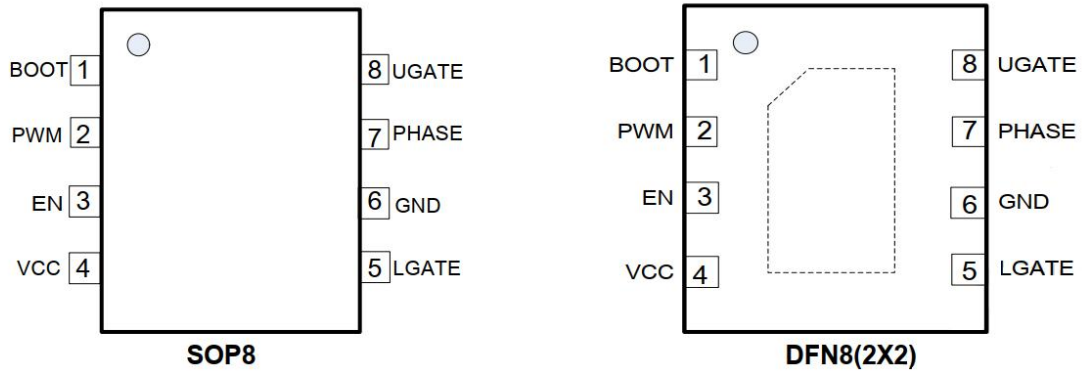
SOP8/DFN2x2-8L:



Reference Design of BOM:

Name	Value	Name	Value
C1	10uF	R1	0
C2	0.1uF	R2	5ohm
C3	22uF	R3	0
Cbst	680nF		

PIN CONFIGURATION



PIN DESCRIPTION

Pin Name	Description	Pin No.
BOOT	Floating bootstrap supply pin for upper gate drive	1
PWM	Input PWM signal for controlling the Driver	2
EN	Logic input for standby mode control	3
VCC	Logic and low-side gate drivers power supply voltage	4
LGATE	Lower gate drive output	5
GND	Ground	6
PHASE	Connect this pin to the source of the high side MOSFET and the drain of the low side MOSFET	7
UGATE	Upper gate drive output	8